

Performance

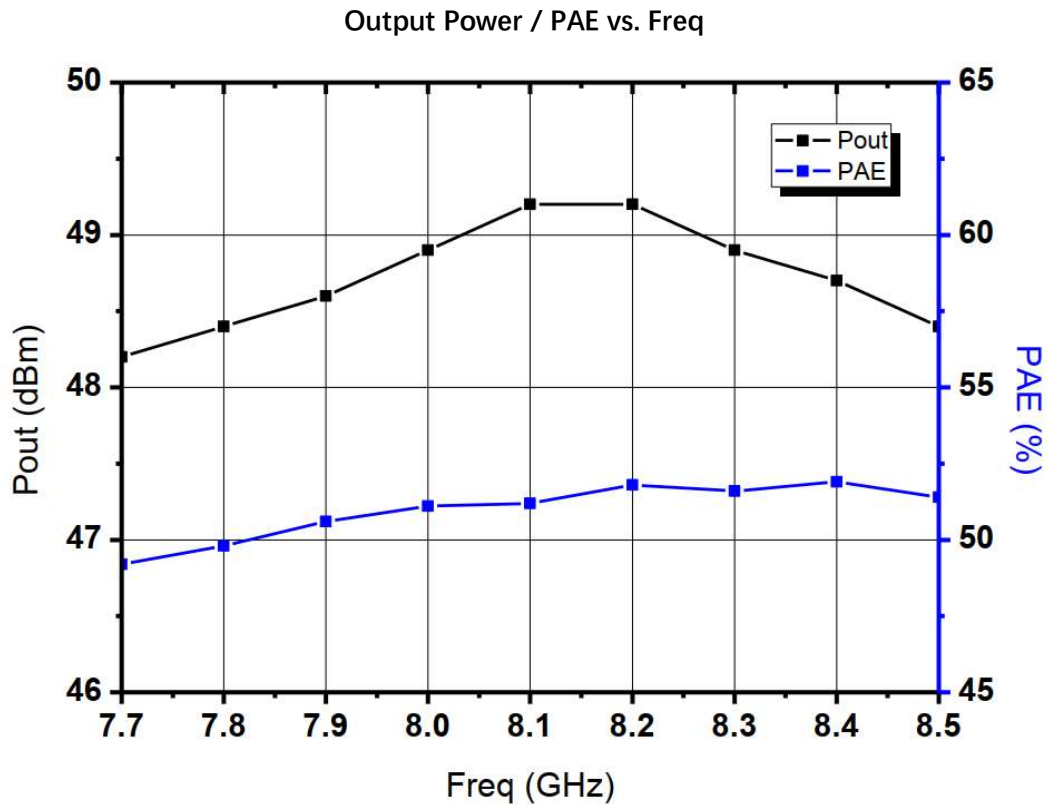
- Frequency: 7.7-8.5GHz
- Output Power: 48dBm (CW)
- Typical Power Gain: 8.0dB
- PAE: 50% (Typ.)
- Bias: 28V/-2.7V@7A
- Package: C164-1
- Size: 24.0*17.4*4.4mm
- Technical Type: 0.35um GaN HEMT



Electrical Specifications (Ta=+25°C, 50Ω system)

Symbol	Parameter	Test Condition	Min	Typical	Max	Unit
P _{out}	Output Power	V _d =28V, V _g =-2.7V I _d ≈8A Freq: 7.7-8.5GHz		48	-	dBm
G _p	Power Gain		-	8	-	dB
η _{add}	Power Added Efficiency		-	50	-	%
ΔG _p	Gain Flatness		-0.8	-	+0.8	dB

Test Curves (Ta=+25°C)

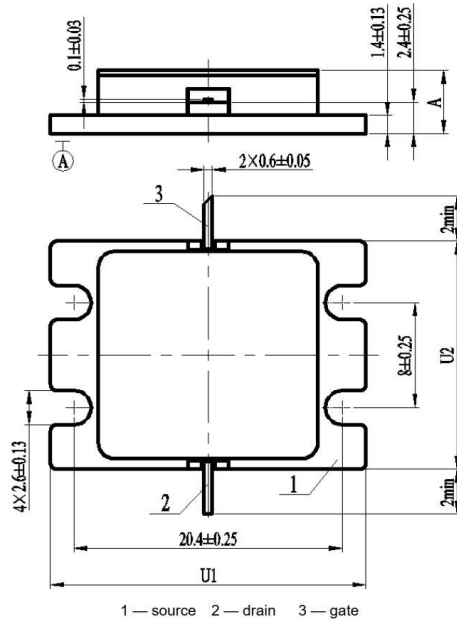


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vds	Drain Bias Voltage	32V	
Vgs	Gate Bias Voltage	-5V	
Pd	DC Power Consumption	100W	25°C
Tch	Channel Temperature	200°C	
Tm	Sintering Temperature	300°C	1min, N2 protection
Tstg	Storage Temperature	-55~175°C	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Symbol	Min	Max
U1	23.8	24.2
U2	17.2	17.6
A		5.2

Application Circuit

